

Title of Invention: SUBSTRATE SUPPORT AND PLASMA PROCESSING APPARATUS

Abstract

5 Provided is a substrate support comprising an electrostatic chuck for supporting a substrate and an edge ring, and a base that supports the electrostatic chuck, the electrostatic chuck including: a first region that has a first upper surface and is configured to support a substrate that is placed on the first upper surface; a second region that has a second upper surface, is provided around the first region,
10 and is configured to support an edge ring that is placed on the second upper surface; a first electrode that is provided in the first region and to which a direct-current voltage is applied; a second electrode that is provided under the first electrode and to which a first bias power is supplied; a third electrode that is provided under the second electrode and to which the first bias power is supplied;
15 and a first gas supply path disposed between the second electrode and the third electrode. The substrate support further includes a first power supply path that is in electrical contact with the second electrode and the third electrode to supply the first bias power.

[Fig.3]